



A Product Line of Diodes Incorporated



ZXTP718MA

20V PNP LOW SATURATION SWITCHING TRANSISTOR

Features and Benefits

- BV_{CEO} > -20V
- I_C = -3.5A Continuous Collector Current
- Low Saturation Voltage (-220mV max @ -1A)
- $R_{SAT} = 64 \text{ m}\Omega$ for a low equivalent On-Resistance
- hFE specified up to -6A for high current gain hold up
- Low profile 0.6mm high package for thin applications
- $R_{\theta JA}$ efficient, 60% lower than SOT23
- 4mm² footprint, 50% smaller than SOT23
- Lead-Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN2020B-3
- Case Material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- Nominal Package Height: 0.6mm
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.01 grams (approximate)

Applications

- MOSFET Gate Driving
- DC-DC Converters
- Charging Circuits
- Power switches
- Motor control

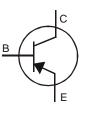
Bottom View Pin-Out

DFN2020B-3



Top View

Bottom View



Device Symbol

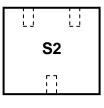
Ordering Information

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP718MATA	S2	7	8	3000
ZXTP718MATC	S2	13	8	10000

Notes: 1. No purposefully added lead.

2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com

Marking Information



S2 = Product Type Marking code

Top View



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit		
Collector-Base Voltage		V _{CBO}	-25			
Collector-Emitter Voltage		V _{CEO}	-20	V		
Emitter-Base Voltage		V _{EBO}	-7			
Peak Pulse Current		Ісм	-6			
Continuous Collector Current	(Note 3)		-3.5			
	(Note 4)	IC	-4.0	A		
Base Current		IB	-1			

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 3)		1.5 12	W	
Linear Derating Factor	(Note 4)		2.45 19.6	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 3)	D	83		
	(Note 4)	R _{θJA}	51	°C/W	
Thermal Resistance, Junction to Lead (Note		R _{0JL}	16.8		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Notes: 3. For a device surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.

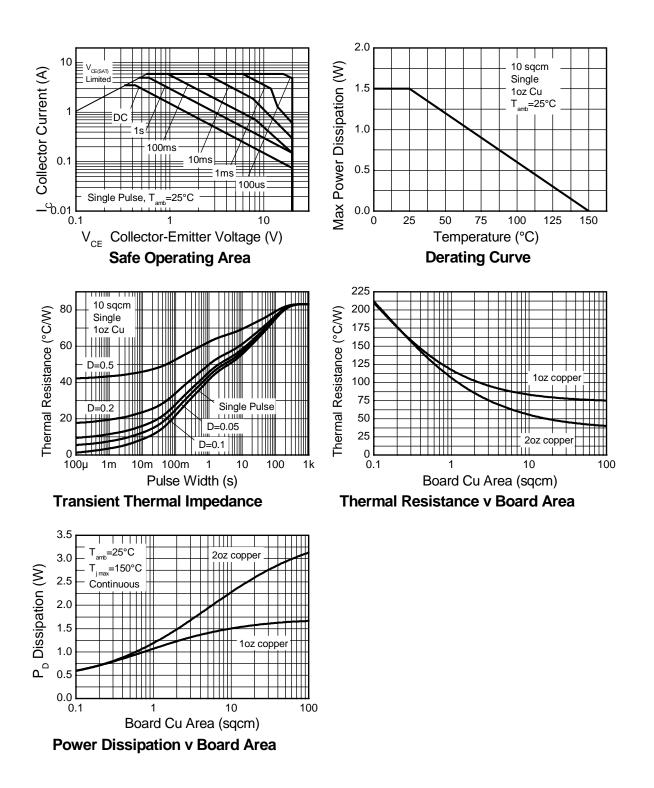
4. Same as note (3), except the device is measured at $t \le 5$ sec.

5. For a single device, thermal resistance from junction to solder-point (at the end of the drain lead).





Thermal Characteristics





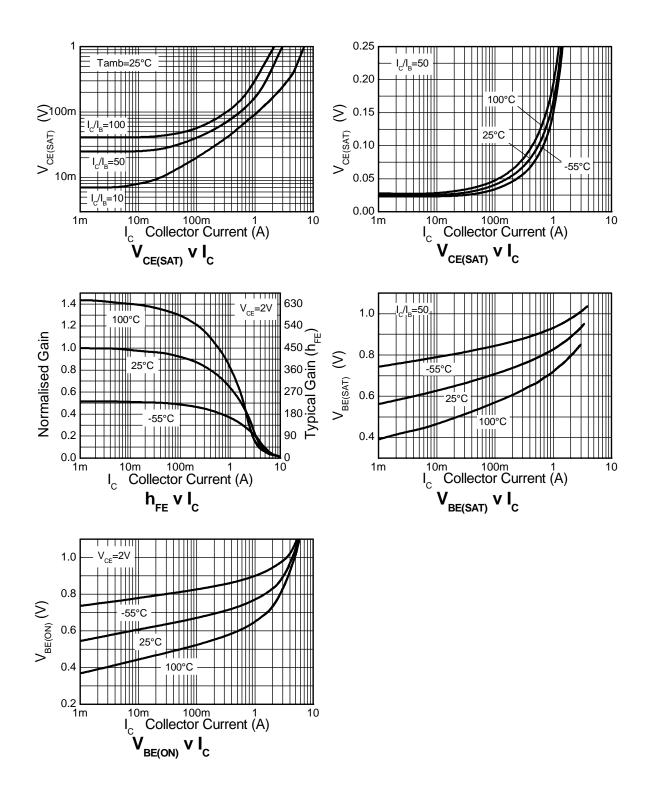
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-25	-35	-	V	I _C = -100 μA
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	-20	-25	-	V	I _C = -10 mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.5	-	V	I _E = -100 μA
Collector Cutoff Current	I _{CBO}	-	-	-100	nA	V _{CB} = -20V
Emitter Cutoff Current	I _{EBO}	-	-	-100	. nA	V _{EB} = -6V
Collector Emitter Cutoff Current	I _{CES}	-	-	-100	nA	V _{CES} = -16V
Static Forward Current Transfer Ratio (Note 6)	h _{FE}	300 300 150 15	475 450 230 30		-	$I_{C} = -10mA, V_{CE} = -2V$ $I_{C} = -100mA, V_{CE} = -2V$ $I_{C} = -2A, V_{CE} = -2V$ $I_{C} = -6A, V_{CE} = -2V$
Collector-Emitter Saturation Voltage (Note 6)	V _{CE(sat)}		-19 -170 -190 -240 -225	-30 -220 -250 -350 -300	mV	$\begin{split} I_{C} &= -0.1A, \ I_{B} &= -10mA \\ I_{C} &= -1A, \ I_{B} &= -20mA \\ I_{C} &= -1.5A, \ I_{B} &= -50mA \\ I_{C} &= -2.5A, \ I_{B} &= -150mA \\ I_{C} &= -3.5A, \ I_{B} &= -350mA \end{split}$
Base-Emitter Turn-On Voltage (Note 6)	V _{BE(on)}	-	-0.87	-0.95	V	I _C = -3.5A, V _{CE} = -2V
Base-Emitter Saturation Voltage (Note 6)	V _{BE(sat)}	-	-1.01	-1.120	V	I _C = -3.5A, I _B = -350mA
Output Capacitance	C _{obo}	-	21	30	pF	V _{CB} =-10V. f = 1MHz
Transition Frequency	f _T	150	180	-	MHz	$V_{CE} = -10V, I_C = -50mA, f = 100MHz$
Turn-On Time	t _{on}	-	40	-	ns	$V_{CC} = -10V, I_{C} = -1A$
Turn-Off Time	t _{off}	-	670	-	ns	$I_{B1} = I_{B2} = -10 \text{mA}$

Notes: 6. Measured under pulsed conditions. Pulse width \leq 300 µs. Duty cycle \leq 2%.



Typical Electrical Characteristics



ZXTP718MA Document Number DS31939 Rev. 4 - 2 Downloaded from <u>Elcodis.com</u> electronic components distributor



Тур

0.60

0.02

0.152

0.25

2.00

1.32

0.66

0.65

2.00

0.58

0.30

0.225

0.63

0.05

0.30

2.075

1.42

0.76

2.075

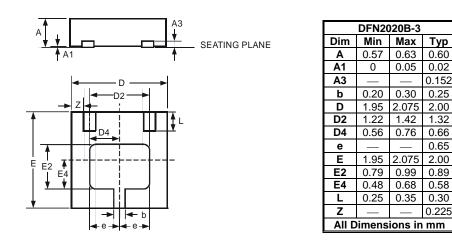
0.68

0.35

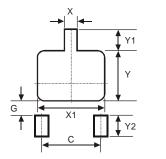
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Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)				
С	1.30				
G	0.24				
Х	0.35				
X1	1.52				
Y	1.09				
Y1	0.47				
Y2	0.50				



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